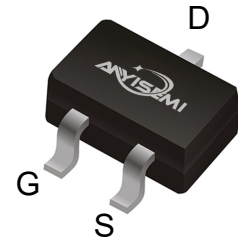
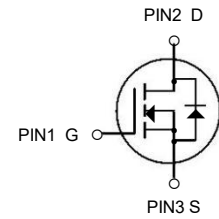


Description

The SI2300ADT-AY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOT-23-3L



N-Channel MOSFET

General Features

$V_{DS} = 20V$ $I_D = 6A$

$R_{DS(ON)} < 27m\Omega @ V_{GS}=4.5V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
SI2300ADT-AY	SOT23-3L	AE9T	3000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	6
		$T_A = 70^\circ C$	3.6
I_{DM}	Drain Current-Pulsed (Note 1)	15	A
P_D	Maximum Power Dissipation	1.25	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	100	$^\circ C/W$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	22.5	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.65	1.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=4.0 A$	-	22	27	m Ω
		$V_{GS}=2.5V, I_D=4.5A$	-	28	40	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=4A$	-	10	-	S
Input Capacitance	C_{iss}	$V_{DS}=8V, V_{GS}=0V,$ $F=1.0MHz$	-	500	-	PF
Output Capacitance	C_{oss}		-	295	-	PF
Reverse Transfer Capacitance	C_{rss}		-	96	-	PF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	11	-	nS
Turn-on Rise Time	t_r		-	30	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	35	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=3A, V_{GS}=4.5V$	-	10	15	nC
Gate-Source Charge	Q_{gs}		-	2.3	-	nC
Gate-Drain Charge	Q_{gd}		-	2.9	-	nC
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=1A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	4.5	A

Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. Surface mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

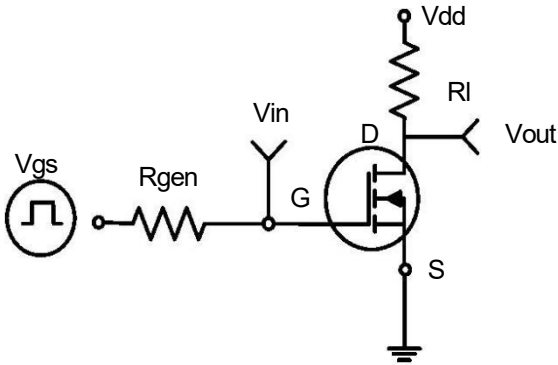


Figure 1: Switching Test Circuit

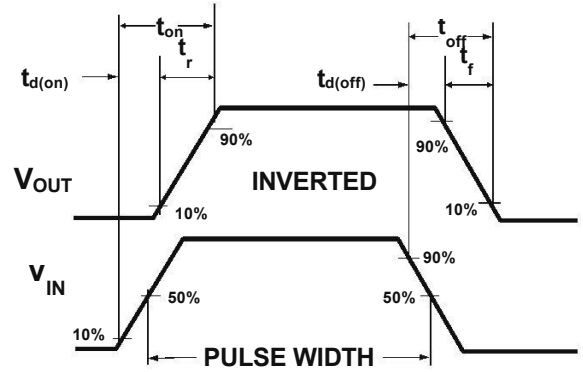


Figure 2: Switching Waveforms

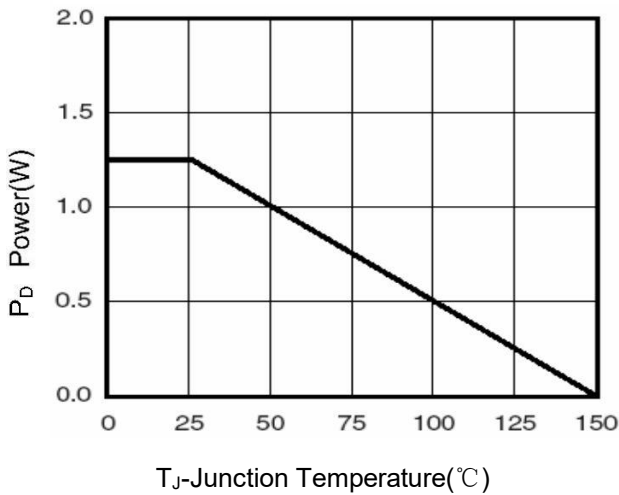


Figure 3 Power Dissipation

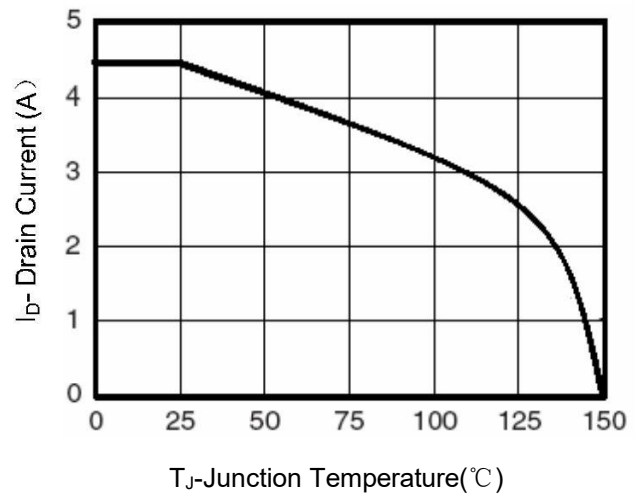


Figure 4 Drain Current

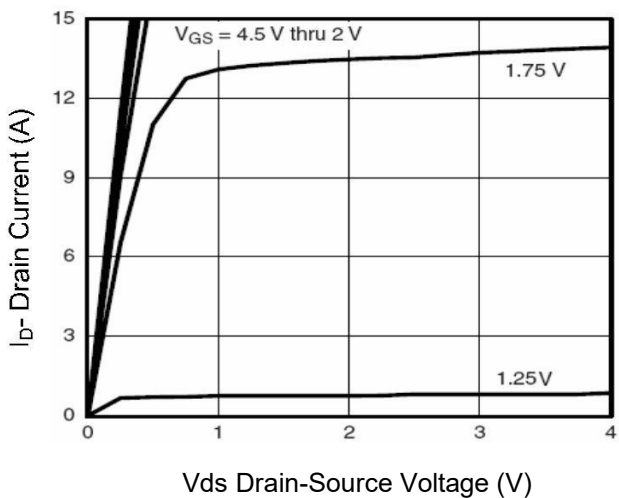


Figure 5 Output Characteristics

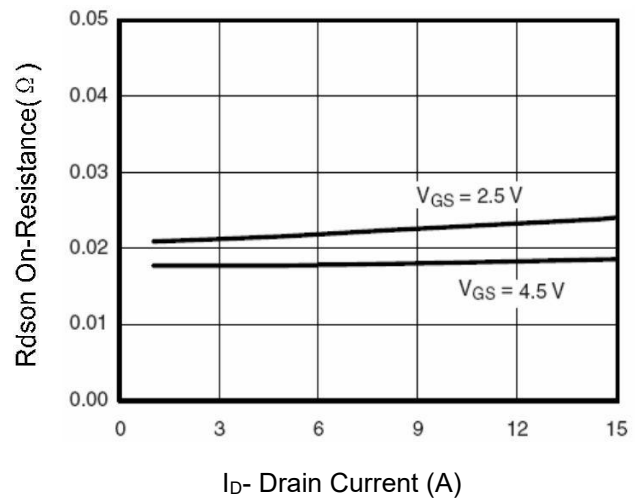


Figure 6 Drain-Source On-Resistance

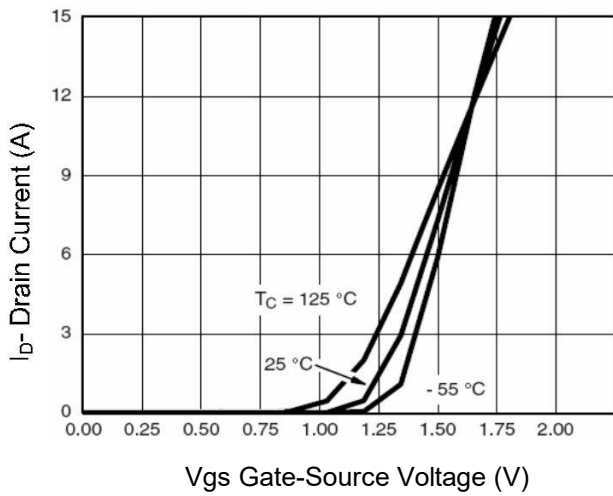


Figure 7 Transfer Characteristics

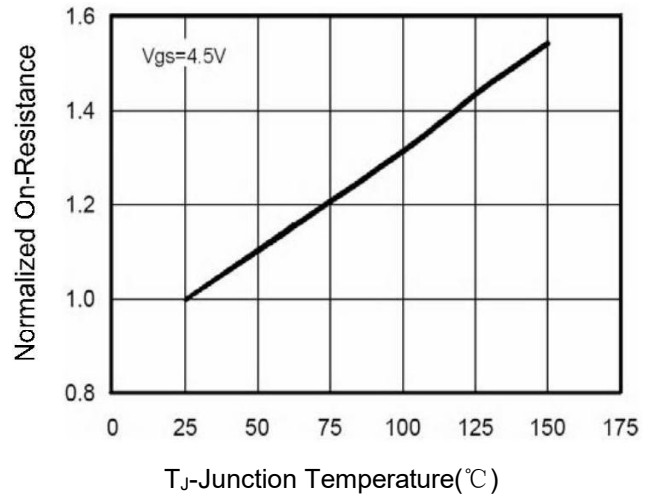


Figure 8 Drain-Source On-Resistance

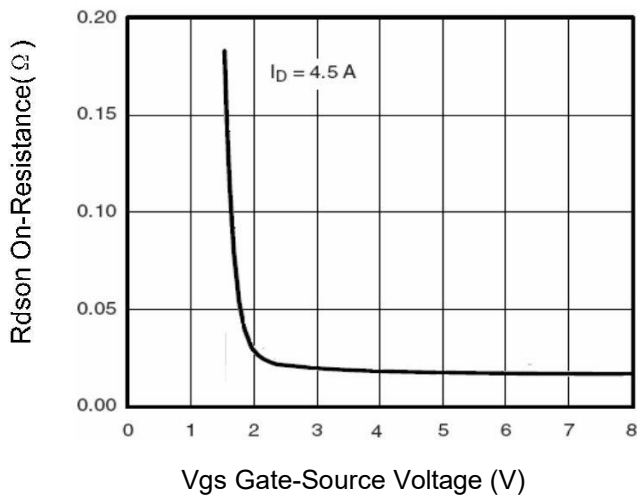


Figure 9 Rds(on) vs. Vgs

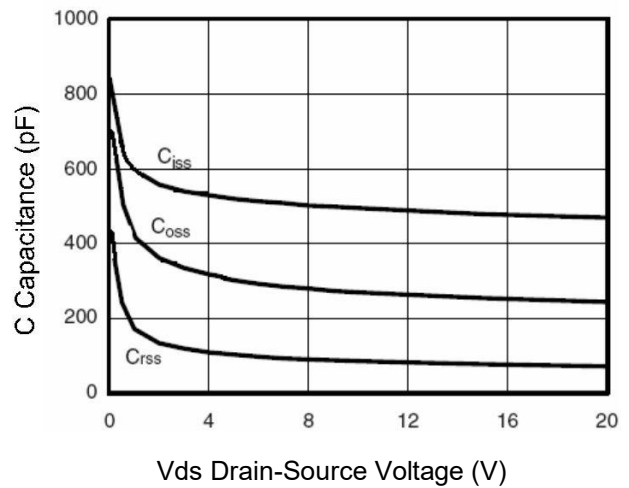


Figure 10 Capacitance vs Vds

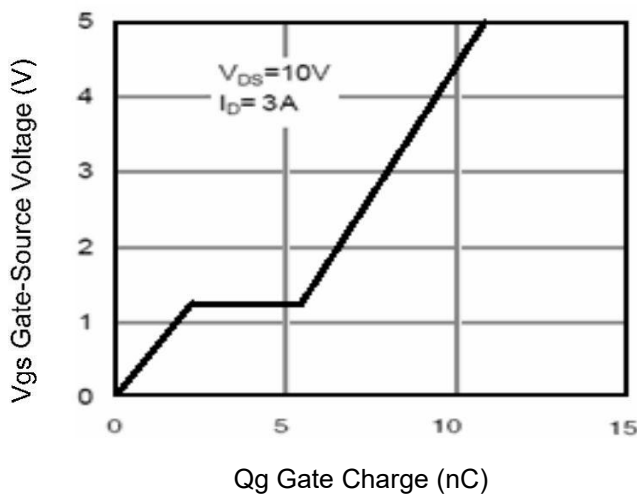


Figure 11 Gate Charge

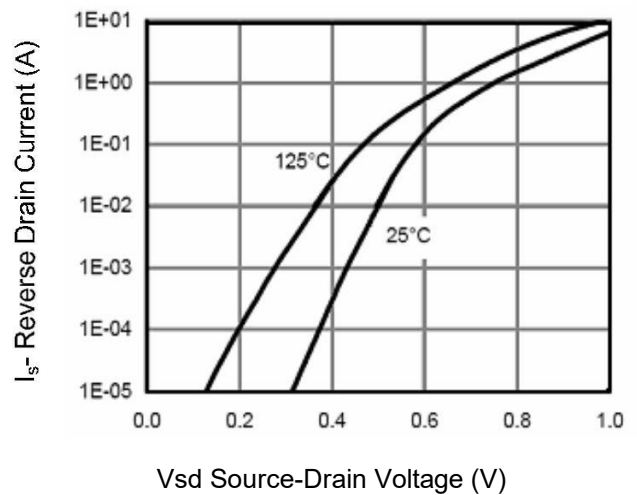


Figure 12 Source-Drain Diode Forward

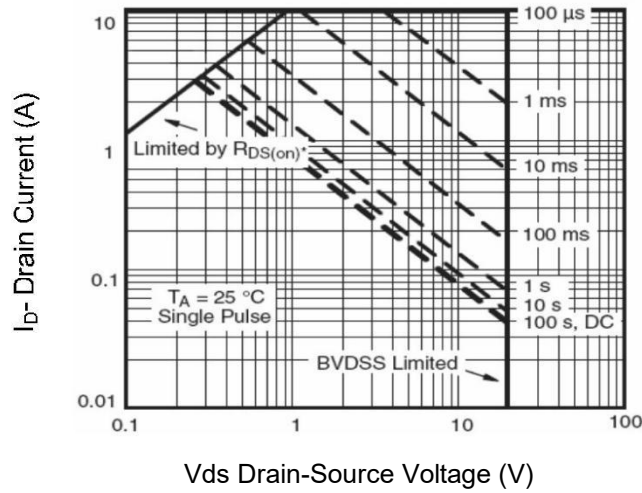


Figure 13 Safe Operation Area

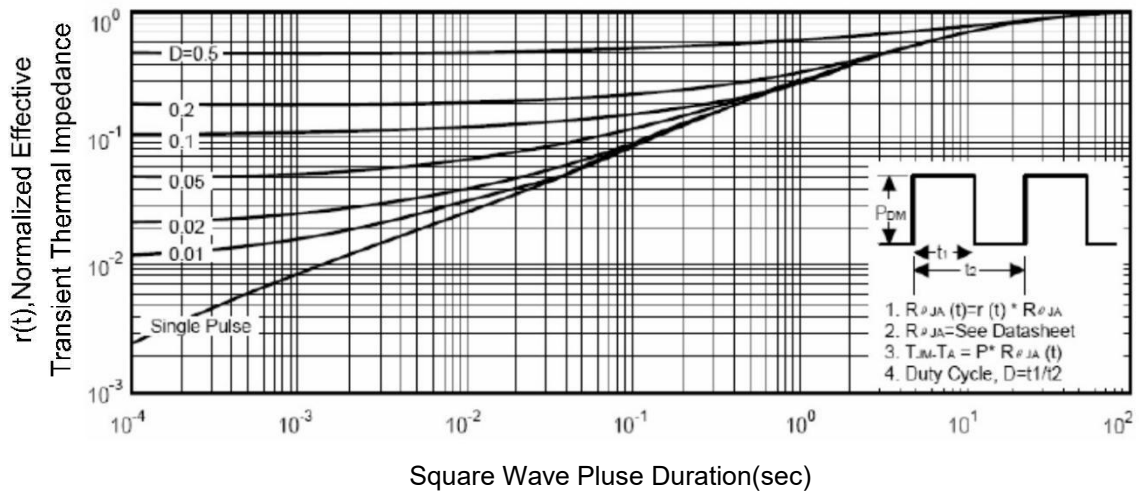
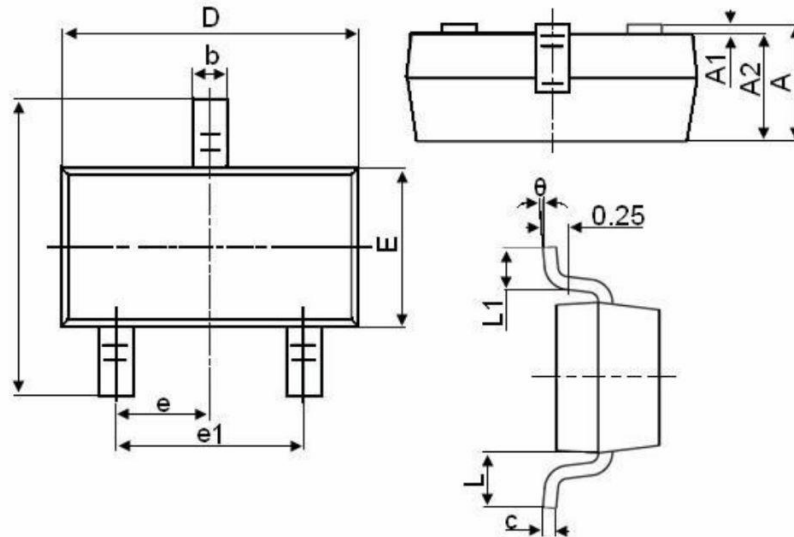


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23-3L Package Information


Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

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